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April 2025

# FQT13N06L

## N-Channel QFET® MOSFET

### 60 V, 2.8 A, 110 mΩ



### General Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### Features

- 2.8 A, 60 V, $R_{DS(on)}$ = 110 mΩ (M[illegible]) @$V_{G}$ = 10 V, $I_D$ = 1.4 A
- Low Gate Charge (Typ. [illegible] nC)
- Low Crss (Typ. 17 pF)
- 100% Avalanche T[illegible]ed


SOT-223
FQT Series

### Absolute Maximum Ratings

$T_C$ = 25°C unless otherwise noted

| Symbol | Parameter | | FQT13N06L | Unit |
|---|---|---|---|---|
| $V_{DSS}$ | Drain-Source Voltage | | 60 | V |
| $I_D$ | Drain Current - Continuous ($T_C$ = 25°C) | | 2.8 | A |
| | - Continuous ($T_C$ = 70°C) | | 2.24 | A |
| $I_{DM}$ | Drain Current - Pulsed | (Note 1) | 11.2 | A |
| $V_{GSS}$ | Gate-Source Voltage | | ± 20 | V |
| $E_{AS}$ | Single Pulsed Avalanche Energy | (Note 2) | 85 | mJ |
| $I_{AR}$ | Avalanche Current | (Note 1) | 2.8 | A |
| $E_{AR}$ | Repetitive Avalanche Energy | (Note 1) | 0.21 | mJ |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | 7.0 | V/ns |
| $P_D$ | Power Dissipation ($T_C$ = 25°C) | | 2.1 | W |
| | - Derate above 25°C | | 0.017 | W/°C |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature Range | | -55 to +150 | °C |
| $T_L$ | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | | 300 | °C |

### Thermal Characteristics

| Symbol | Parameter | Typ | Max | Unit |
|---|---|---|---|---|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient * | -- | 60 | °C/W |

* When mounted on the minimum pad size recommended(PCB mount).

## Electrical Characteristics

$T_C$ = 25°C unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}$ = 0 V, $I_D$ = 250 μA | 60 | -- | -- | V |
| $\Delta BV_{DSS}$ / $\Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250 μA, Referenced to 25°C | -- | 0.05 | -- | V/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 60 V, $V_{GS}$ = 0 V | -- | -- | 1 | μA |
| | | $V_{DS}$ = 48 V, $T_C$ = 125°C | -- | -- | 10 | μA |
| $I_{GSSF}$ | Gate-Body Leakage Current, Forward | $V_{GS}$ = 20 V, $V_{DS}$ = 0 V | -- | -- | 100 | nA |
| $I_{GSSR}$ | Gate-Body Leakage Current, Reverse | $V_{GS}$ = -20 V, $V_{DS}$ = 0 V | -- | -- | -100 | nA |
| **On Characteristics** | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 μA | 1 | -- | 2.5 | V |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS}$ = 10 V, $I_D$ = 1.4 A | -- | 0.088 | 0.11 | Ω |
| | | $V_{GS}$ = 5 V, $I_D$ = 1.4 A | -- | 0.11 | 0.14 | Ω |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 25 V, $I_D$ = 1.4 A (Note 4) | -- | 4.1 | -- | S |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 25 V, $V_{GS}$ = 0 V, f = 1.0 MHz | -- | 270 | 350 | pF |
| $C_{oss}$ | Output Capacitance | | -- | 95 | 125 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | -- | 17 | 23 | pF |
| **Switching Characteristics** | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}$ = 30 V, $I_D$ = 6.8 A, $R_G$ = 25 Ω (Note 4, 5) | -- | 8 | 25 | ns |
| $t_r$ | Turn-On Rise Time | | -- | 90 | 190 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | -- | 20 | 50 | ns |
| $t_f$ | Turn-Off Fall Time | | -- | 40 | 90 | ns |
| $Q_g$ | Total Gate Charge | $V_{DS}$ = 48 V, $I_D$ = 13.6 A, $V_{GS}$ = 5 V (Note 4, 5) | -- | 4.8 | 6.4 | nC |
| $Q_{gs}$ | Gate-Source Charge | | -- | 1.6 | -- | nC |
| $Q_{gd}$ | Gate-Drain Charge | | -- | 2.7 | -- | nC |
| **Drain-Source Diode Characteristics and Maximum Ratings** | | | | | | |
| $I_S$ | Maximum Continuous Drain-Source Diode Forward Current | | -- | -- | 2.8 | A |
| $I_{SM}$ | Maximum Pulsed Drain-Source Diode Forward Current | | -- | -- | 11.2 | A |
| $V_{SD}$ | Drain-Source Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = 2.8 A | -- | -- | 1.5 | V |
| $t_{rr}$ | Reverse Recovery Time | $V_{GS}$ = 0 V, $I_S$ = 13.6 A, $dI_F$ / dt = 100 A/μs (Note 4) | -- | 45 | -- | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | -- | 45 | -- | nC |

**Notes:**
1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 12.6 mH, $I_{AS}$ = 2.8 A, $V_{DD}$ = 25 V, $R_G$ = 25 Ω, starting $T_J$ = 25°C.
3. $I_{SD}$ ≤ 13.6 A, di/dt ≤ 300 A/μs, $V_{DD}$ ≤ $BV_{DSS}$, starting $T_J$ = 25°C.
4. Pulse test : pulse width ≤ 300 μs, Duty cycle ≤ 2%.
5. Essentially independent of operating temperature.

## Typical Characteristics

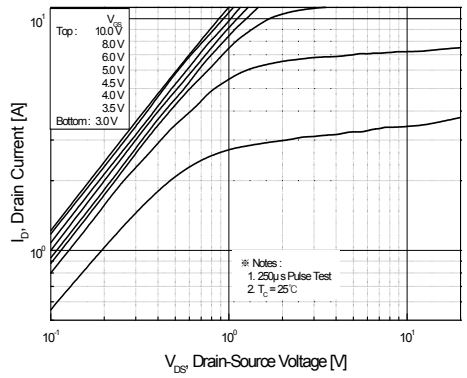



**Figure 1. On-Region Characteristics**

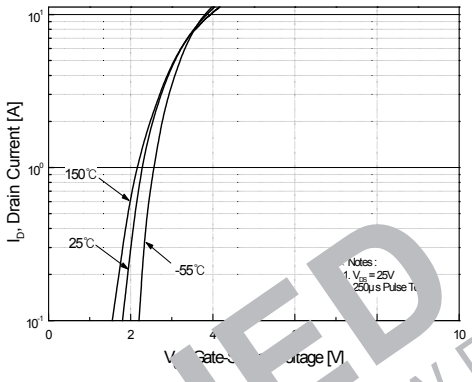



**Figure 2. Transfer Characteristics**

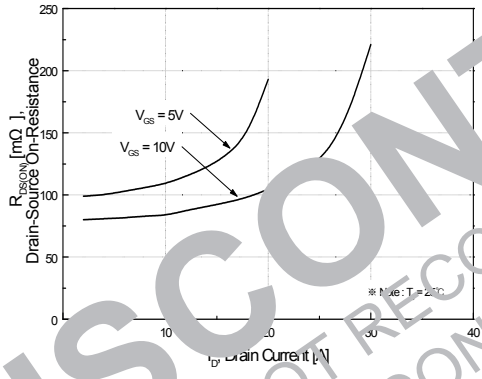



**Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage**

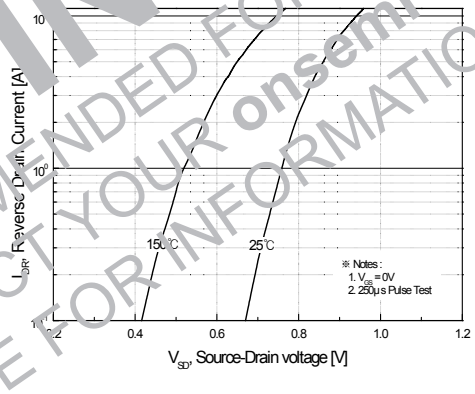



**Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature**

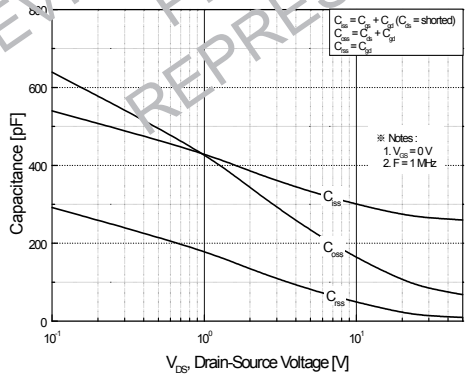



**Figure 5. Capacitance Characteristics**

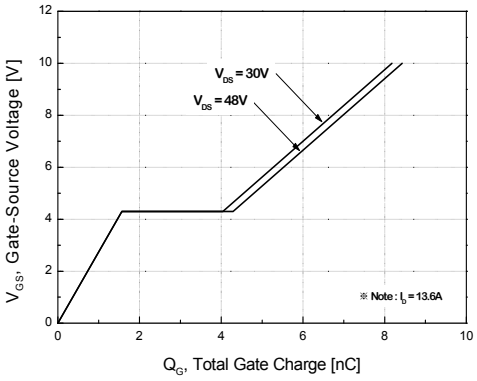



**Figure 6. Gate Charge Characteristics**

## Typical Characteristics (Continued)

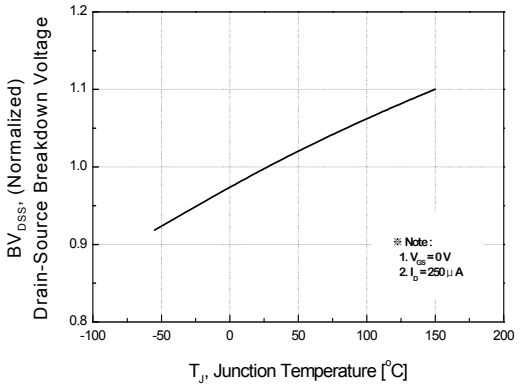



**Figure 7. Breakdown Voltage Variation vs Temperature**

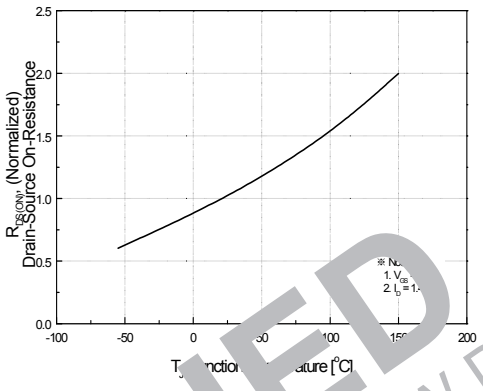



**Figure 8. On-Resistance Variation vs Temperature**

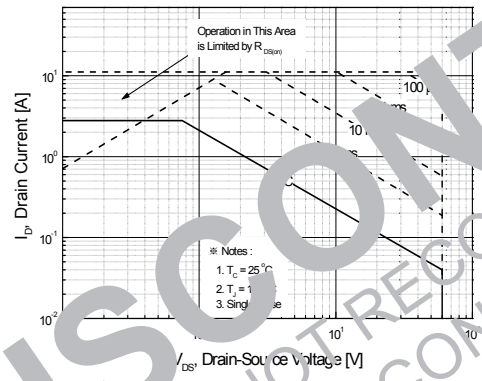



**Figure 9. Maximum Safe Operating Area**

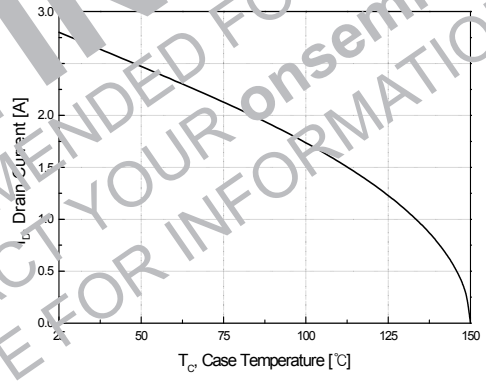



**Figure 10. Maximum Drain Current vs Case Temperature**

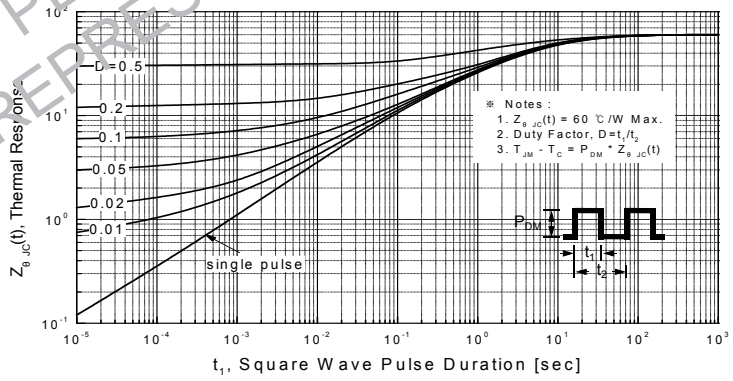



**Figure 11. Transient Thermal Response Curve**

**Figure 12. Gate Charge Test Circuit & Waveform**

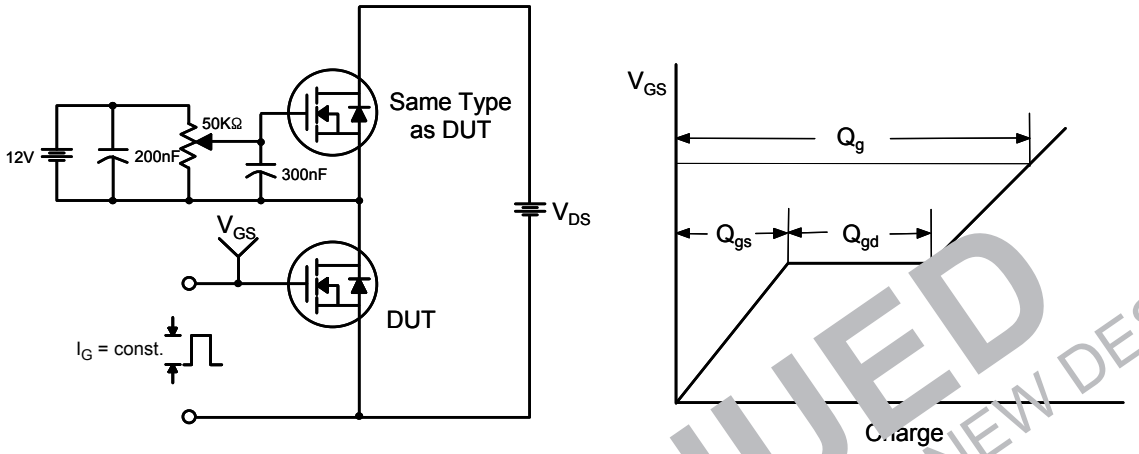



**Figure 13. Resistive Switching Test Circuit & Waveforms**

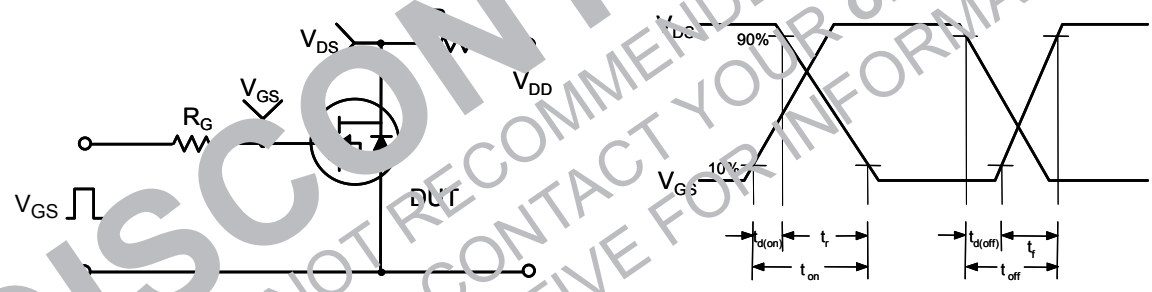



**Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms**

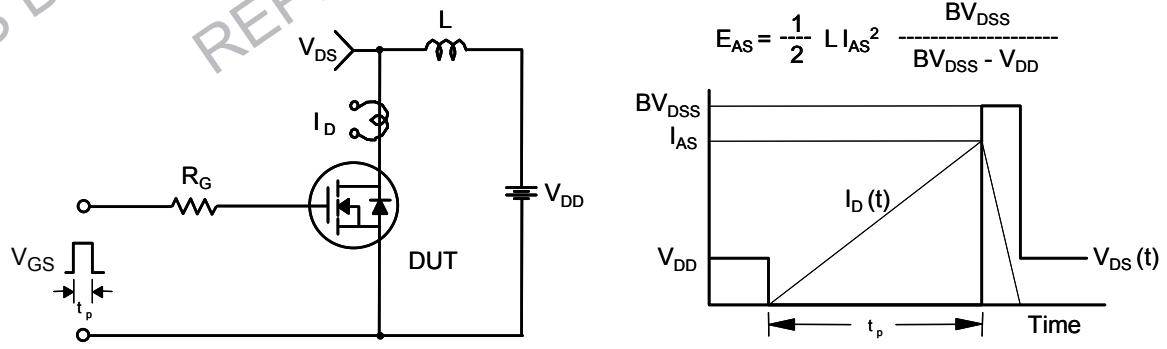
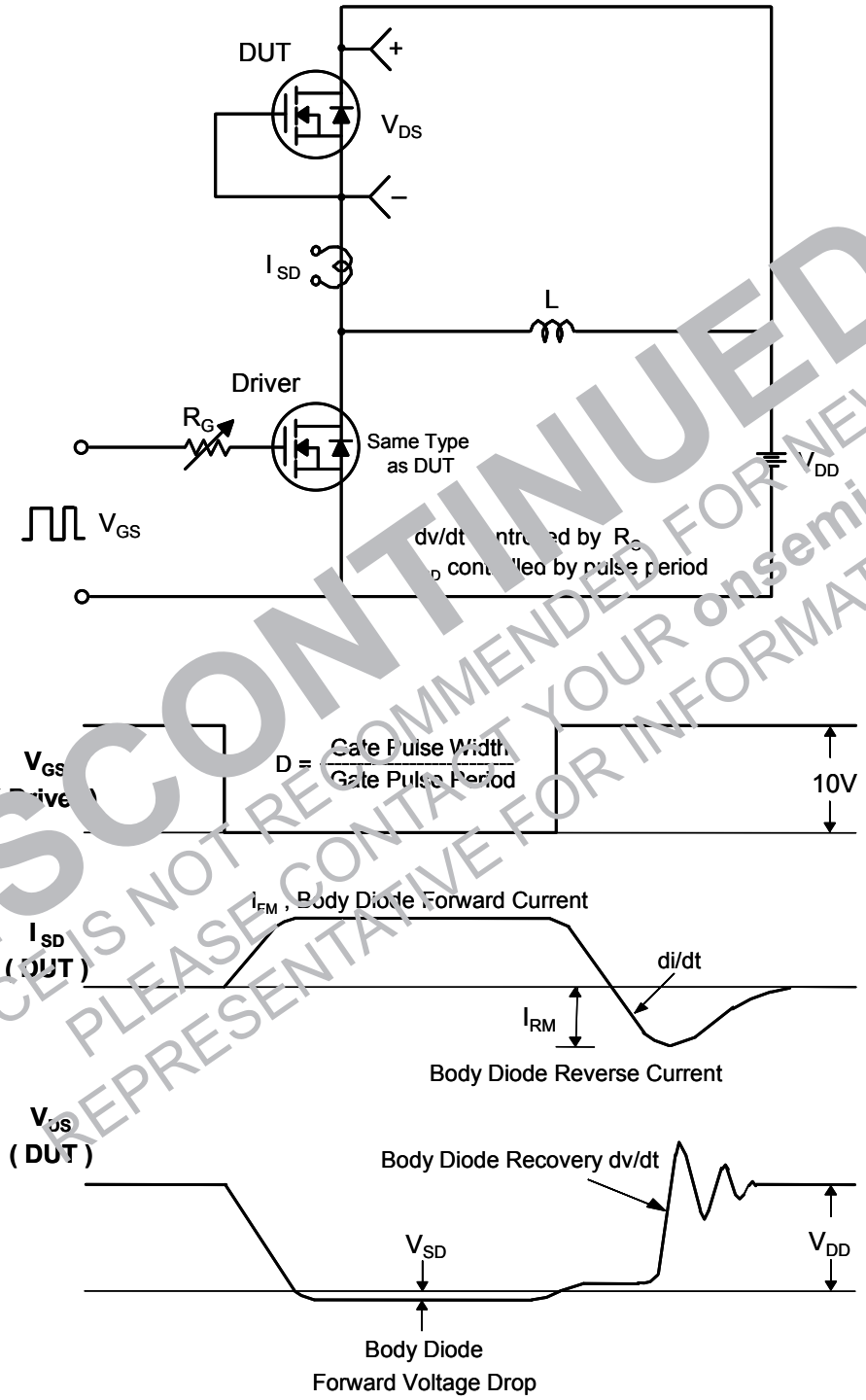
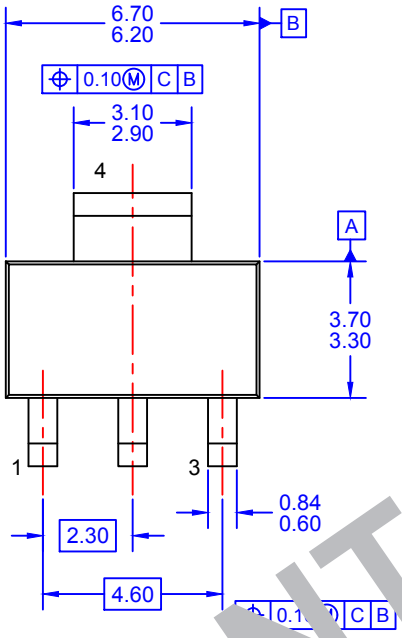
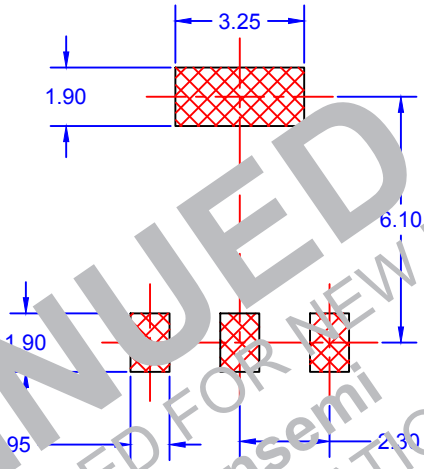


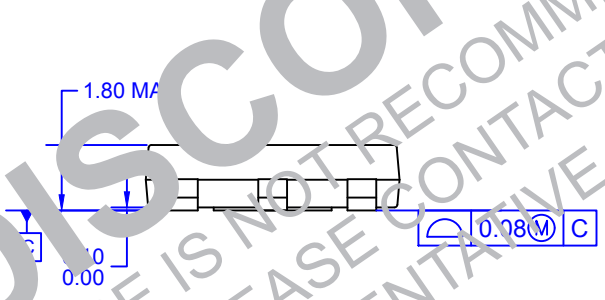
**Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms**

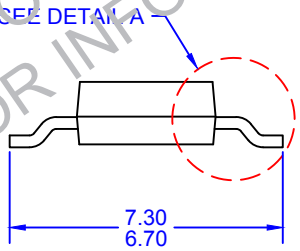




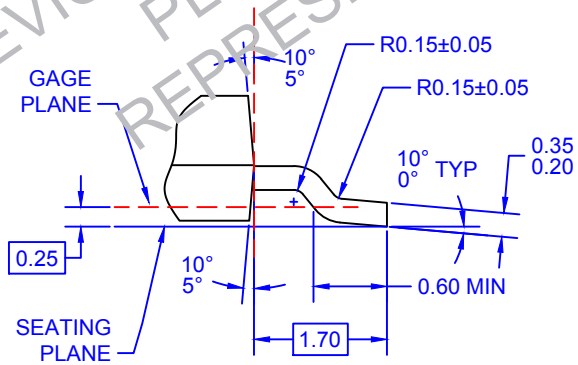

LAND PATTERN RECOMMENDATION




NOTES: UNLESS OTHERWISE SPECIFIED

A) DRAWING BASED ON JEDEC REGISTRATION TO-261C, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
E) LANDPATTERN NAME: SOT230P700X180-4BN
F) DRAWING FILENAME: MKT-MA04AREV3




DETAIL A
SCALE: 2:1

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